Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT186A "full pack" plastic package. This triac is intended for use in motor control circuits where very high blocking voltage, high static and dynamic dV/dt as well as high dl_{com}/dt can occur. This "series C" triac will commutate the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

2. Features and benefits

- 3Q technology for improved noise immunity
- · High commutation capability with maximum false trigger immunity
- High immunity to false tun on by dV/dt
- · Isolated mounting base package
- · Planar passivated for voltage ruggedness and reliability
- · Triggering in three quadrants only
- Very high voltage capability

3. Applications

- Compressor starting controls
- General purpose motor controls
- · Reversing induction motor control e.g. window shutters, blinds and sun shades

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	1000	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 92 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	-	4	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	-	25	Α
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics		·			
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	2	6	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	2	8	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G-;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	2	20	35	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	
2	T2	main terminal 2		T2_DT1
3	G	gate		sym051
mb	n.c.	mounting base; isolated		Symoor
			$ \left(\begin{array}{ccc} \prod_{1 \ 2 \ 3} \end{array}\right) $	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA204X-1000C	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	1000	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 92$ °C; Fig. 1; Fig. 2; Fig. 3	-	4	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig 4; Fig 5	-	25	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	27	А
I ² t	I ² t for fusing	t _p = 10 ms; SIN	-	3.1	A ² s
dl _⊤ /dt	rate of rise of on-state current	I _G = 70 mA	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
P_{GM}	peak gate power		-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

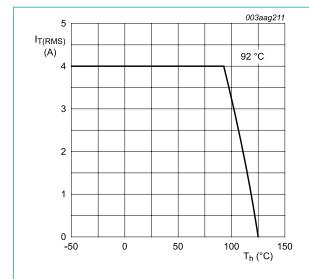
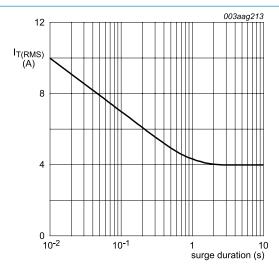
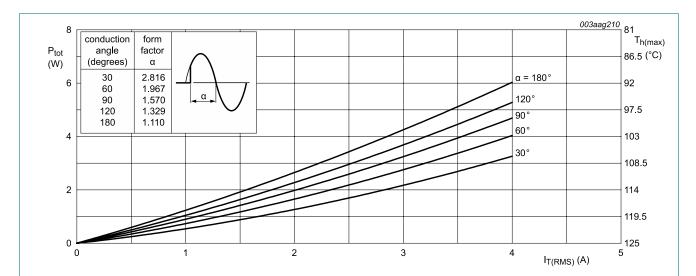


Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values



 $f = 50 Hz; T_h = 92 °C$

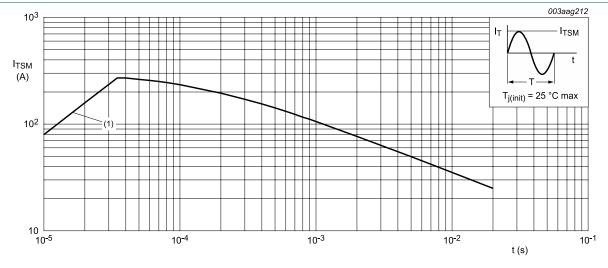
Fig. 2. RMS on-state current as a function of surge duration; maximum values



 α = conduction angle

 $a = form factor = I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



 $t_p \le 20 \text{ ms};$ (1) $dl_T/dt \text{ limit}$

Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

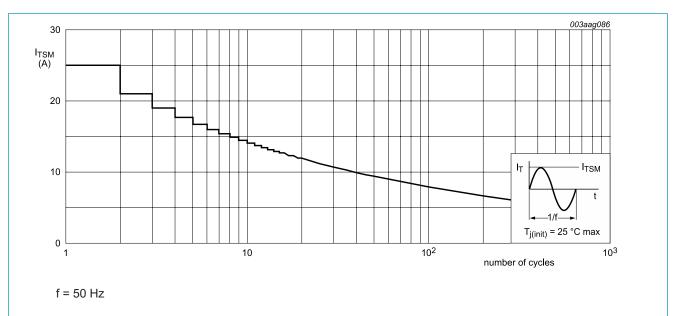
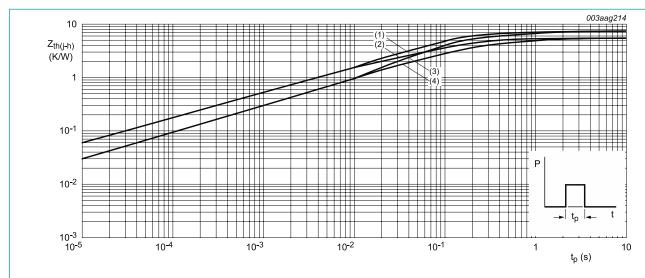


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to	full cycle or half cycle; with heatsink compound; Fig 6	-	-	5.5	K/W
	heatsink	full cycle or half cycle; without heatsink compound; Fig 6	-	-	7.2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

9. Isolation Characteristics

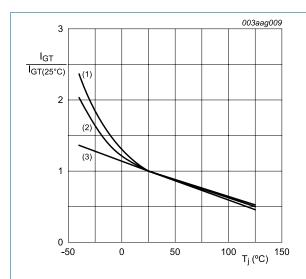
Table 6. Isolation Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; $T_h = 25$ °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T _h = 25 °C	-	10	-	pF

10. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	2	6	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 ^{\circ}\text{C; } Fig. 7$	2	8	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	2	20	35	mA
I _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	20	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	20	mA
V _T	on-state voltage	I _T = 5 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$	0.25	0.4	-	V
I _D	off-state current	V _D = 1000 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 670 V; T_j = 125 °C; exponential waveform; gate open circuit	1000	500	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 4 A; dV_{com}/dt = 20 V/ μ s; (without snubber condition); gate open circuit	3	30	-	A/ms
t _{gt}	gate-controlled turn-on time	$I_{TM} = 12 \text{ A}; V_D = 1000 \text{ V}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

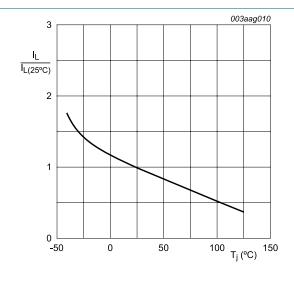


Fig. 8. Normalized latching current as a function of junction temperature

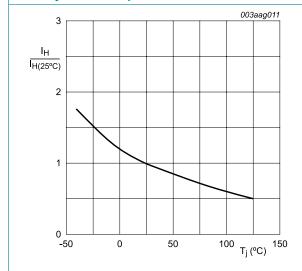
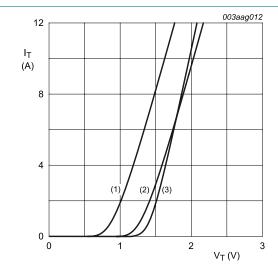


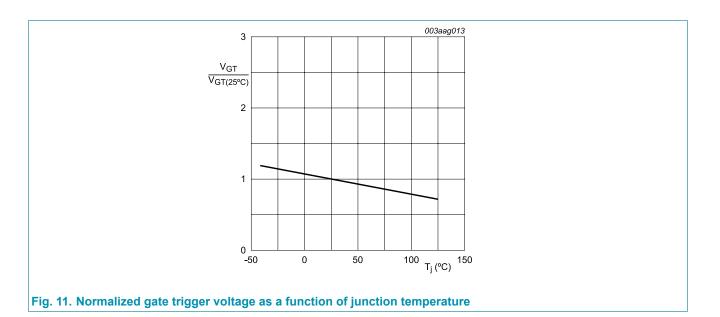
Fig. 9. Normalized holding current as a function of junction temperature



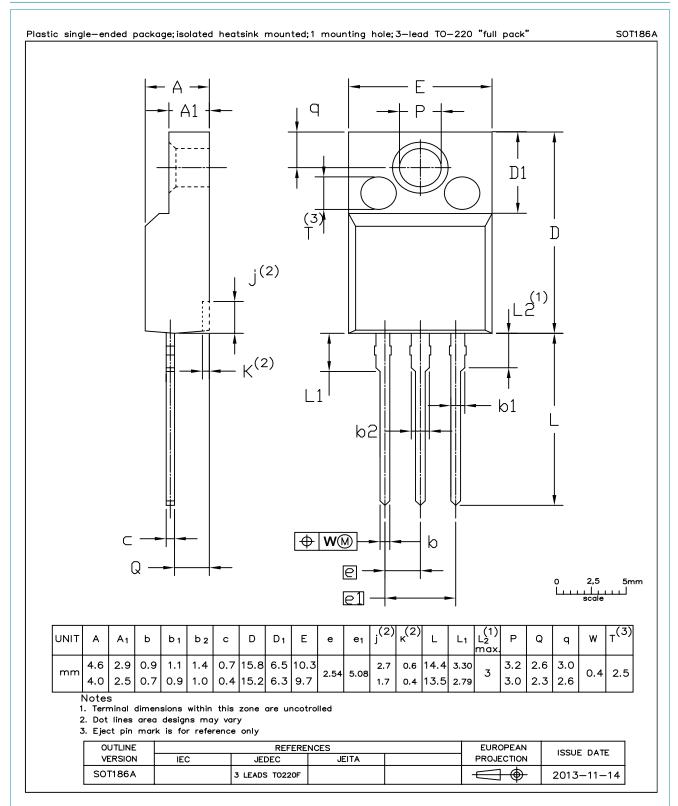
 V_o = 1.22 V; R_s = 0.04 Ω (1) T_i = 125 °C; typical values

(2) $T_j = 125$ °C; maximum values (3) $T_i = 25$ °C; maximum values

Fig. 10. On-state current as a function of on-state voltage



11. Package outline



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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For more information, please visit: http://www.ween-semi.com For sales office addresses, please send an email to: salesaddresses@ween-semi.com Date of release: 26 July 2018

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